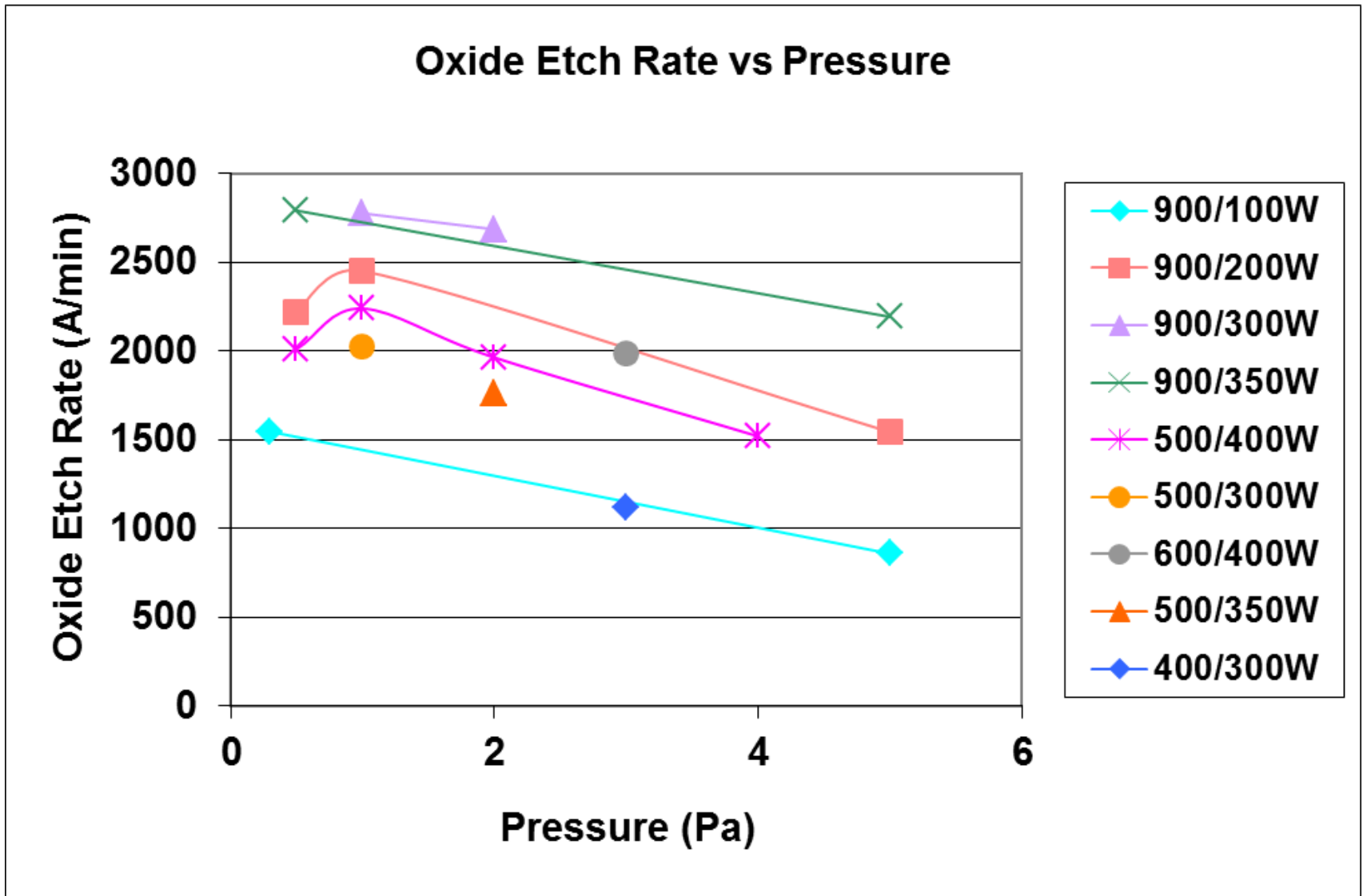


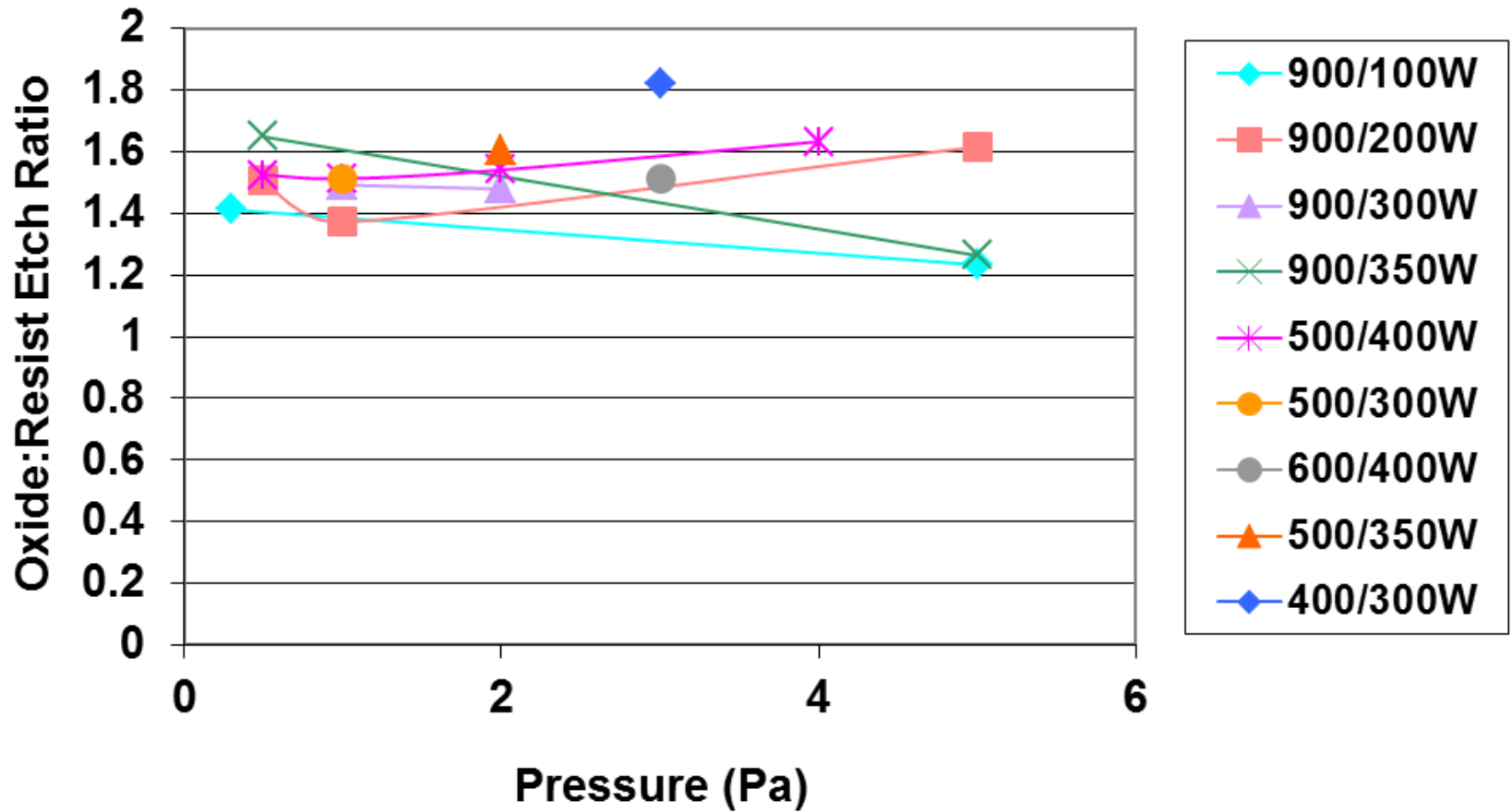
# Panasonic 1 Process Variations for CHF<sub>3</sub>-Based SiO<sub>2</sub> etching

Based on Recipe 118, SiOVert, CHF<sub>3</sub> flow = 40sccm

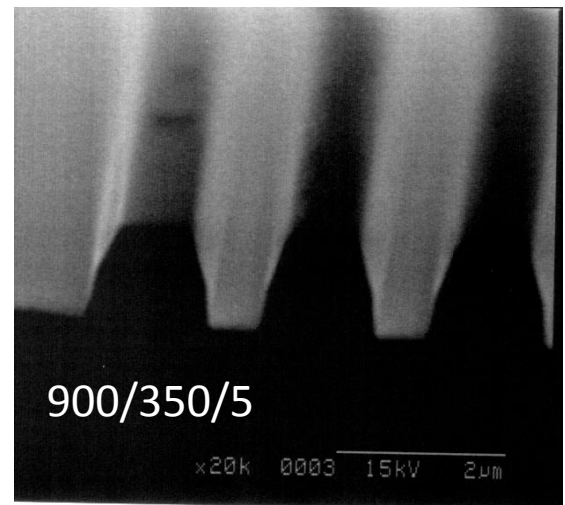
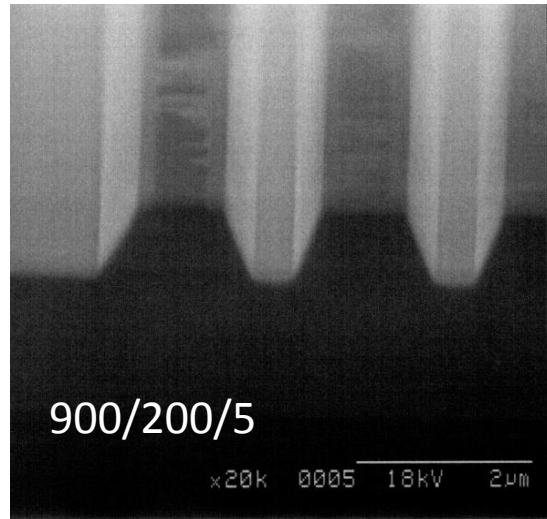
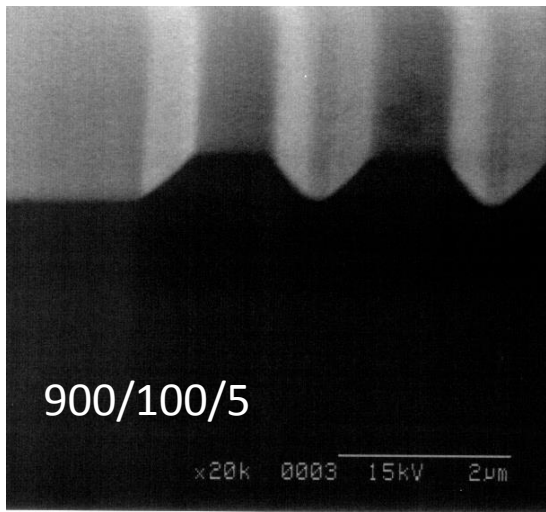
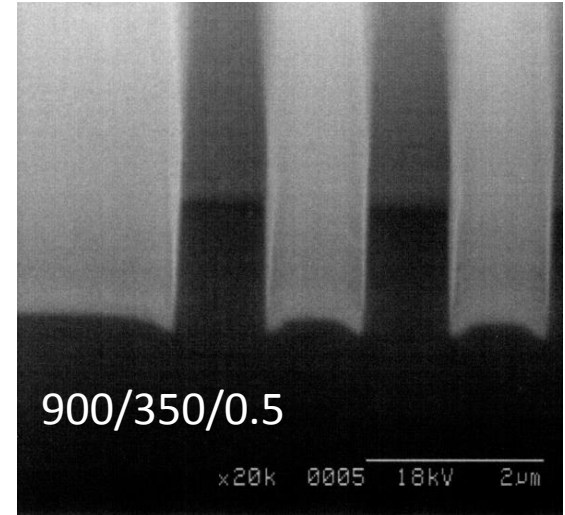
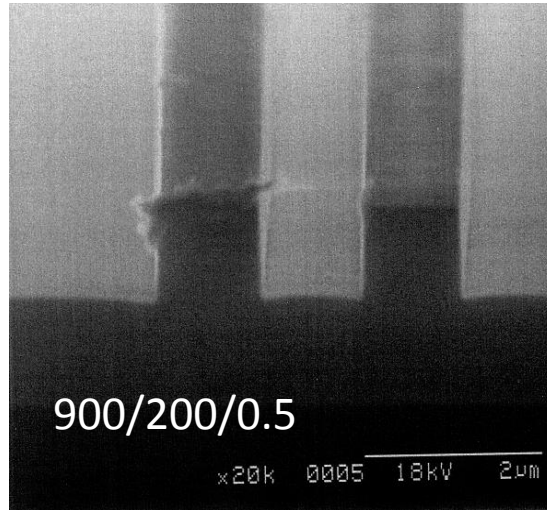
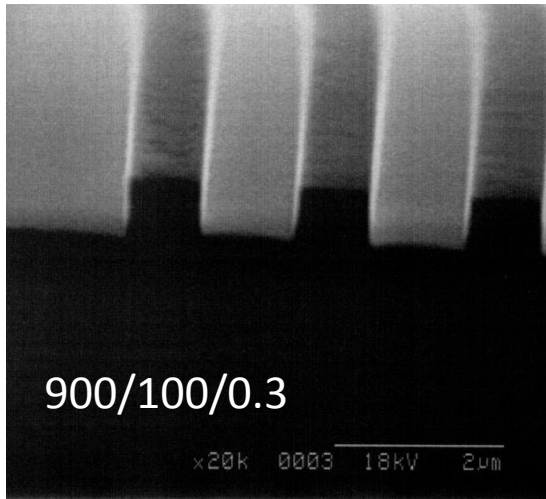


Based on Recipe 118, SiOVert, CHF<sub>3</sub> flow = 40sccm

### Oxide:Resist Etch Ratio vs Pressure



Based on Recipe 118, SiOVert, CHF<sub>3</sub> flow = 40sccm



ICP/Bias/Pressure